

INTEGRATED CIRCUIT HAVING A DOPED POROUS
DIELECTRIC AND METHOD OF MANUFACTURING THE SAME

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ABSTRACT OF THE DISCLOSURE

10 In one aspect of the invention, a method for forming
an integrated circuit having an at least substantially
doped porous dielectric includes forming a semiconductor
device. The semiconductor device includes at least a
portion of a semiconductor substrate. The method also
includes forming a dielectric layer disposed outwardly from
the semiconductor substrate and surrounding at least a
15 portion of the semiconductor device. The dielectric layer
includes an at least substantially porous dielectric
material doped with at least one dopant. In addition, the
method includes forming a contact layer disposed outwardly
from the dielectric layer and operable to provide
20 electrical connection to the semiconductor device.